BYC8-600P

Hyperfast power diode

24 July 2012

Product data sheet

1. Product profile

1.1 General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

1.2 Features and benefits

- Fast switching
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

1.3 Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	SQW; $\delta = 0.5$; $T_{mb} \le 130$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	8	А
Static characte	eristics						
V _F	forward voltage	I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	12	18	ns





Hyperfast power diode

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC8-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	SQW; δ = 0.5; $T_{mb} \le 130$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8	A
I _{FRM}	repetitive peak forward current	SQW; δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 130$ °C	-	16	Α
I _{FSM}	non-repetitive peak forward	SIN; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; Fig. 4	-	91	Α
	current	SIN; $t_p = 8.3 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; Fig. 4	-	100	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

Hyperfast power diode

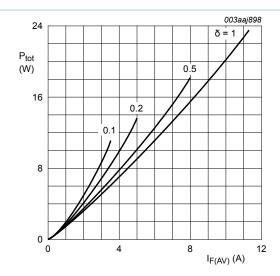


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

 $V_O = 1.581 \text{ V}; \text{ R}_S = 0.043 \Omega$

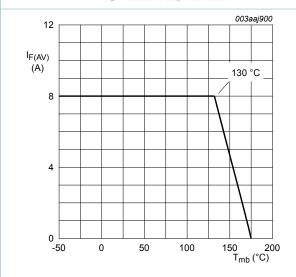


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

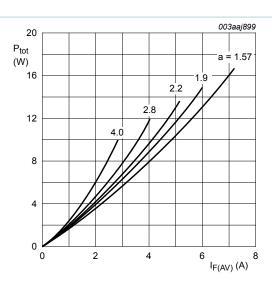


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 $V_O = 1.581 \text{ V}; R_S = 0.043 \Omega$

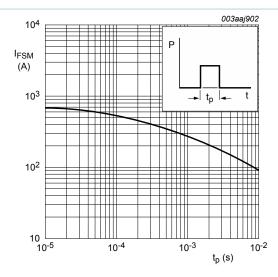


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.5	K/W

BYC8-600P

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

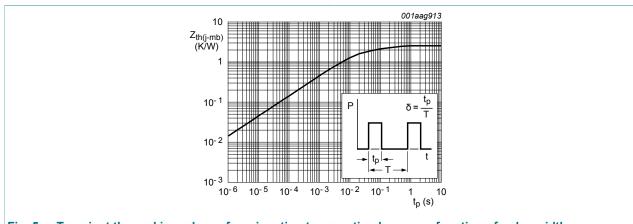


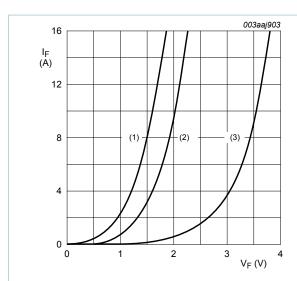
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μA
		V _R = 600 V; T _j = 125 °C	-	-	200	μA
Dynamic cha	racteristics		'		'	
Q _r	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17	-	nC
		I _F = 8 A; V _R = 200 V; dI _F /dt = 200 A/s; T _j = 125 °C; <u>Fig. 7</u>	-	90	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/s}$; $I_j = 25 \text{ °C}$; Fig. 7	-	12	18	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	А
		I _F = 8 A; V _R = 200 V; dI _F /dt = 200 A/s; T _j = 125 °C; <u>Fig. 7</u>	-	-	6	А

Hyperfast power diode





(1) $T_j = 125$ °C; typical values; (2) $T_j = 125$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_O = 1.581$ V; $R_S = 0.043$ Ω

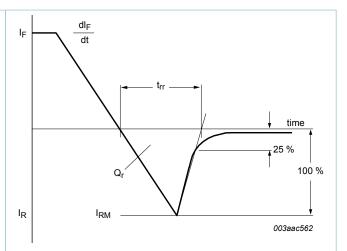
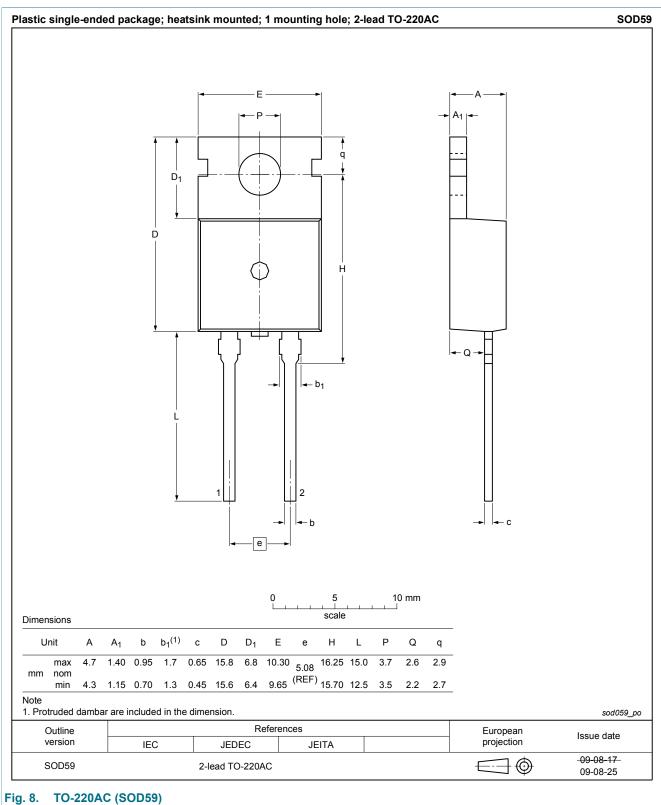


Fig. 7. Reverse recovery definitions; ramp recovery

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Package outline



6/9

Hyperfast power diode

8. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Hyperfast power diode

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Hyperfast power diode

9. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	4
7	Package outline	6
8	Legal information	7
8.1	Data sheet status	7
8.2	Definitions	7
8.3	Disclaimers	7
8.4	Trademarks	8

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